Vishay Semiconductors

Hyperfast Rectifier, 30 A FRED Pt[®] G5



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LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTE	RISTICS
I _{F(AV)}	30 A
V _R	600 V
V _F at I _F at 125 °C	1.15 V
t _{rr} (typ.)	25 ns
T _J max.	175 °C
Package	D ² PAK 2L (TO-263AB 2L)
Circuit configuration	Single

FEATURES

- · Best in class forward voltage drop and switching losses trade off
- · Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- AEC-Q101 qualified, meets JESD 201 class 1A whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for soft switched and resonant converters, as well as medium frequency hard switching converters. This device is specifically designed to improve efficiency of high speed LLC output rectification stages of EV / HEV battery charging stations and high frequency stages of UPS applications.

MECHANICAL DATA

Case: D²PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V _{RRM}		600	V						
Average rectified forward current	I _{F(AV)}	T _C = 113 °C, D = 0.50	30	А						
Repetitive peak forward current	I _{FRM}	T _C = 113 °C, D = 0.50, f = 20 kHz	60							
Non-repetitive peak surge current	I _{FSM}	$T_C = 25 \text{ °C}, t_p = 10 \text{ ms}, \text{ sine wave}$	330							
Operating junction and storage temperature	T _J , T _{Stg}		-55 to +175	°C						

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL TEST CONDITIONS					UNITS				
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-					
	VF	I _F = 30 A	-	1.3	1.6	V				
Forward voltage	۷F	I _F = 30 A, T _J = 125 °C	-	1.15	-					
Deverse leekees surrent		V _R = V _R rated	-	-	20					
Reverse leakage current	IR	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA				
Junction capacitance	CT	V _R = 200 V	-	36	-	pF				
Series inductance	L _S	Measured to lead 5 mm from package body	-	8	-	nH				

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)											
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS					
		I _F = 1.0 A,dI _F /dt =	100 A/µs, V _R = 30 V	-	25	-					
Reverse recovery time	t _{rr}	T _J = 25 °C		-	41	-	ns				
		T _J = 125 °C		-	58	-					
Pook receivery ourrent	1	T _J = 25 °C	$I_F = 20 A$	-	19	-	A				
Peak recovery current	I _{RRM}	T _J = 125 °C	dl _F /dt = 1000 A/µs V _R = 400 V	-	32	-					
D	0	T _J = 25 °C		-	419	-	nC				
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	1176	-					
Poverse recovery time	+	T _J = 25 °C		-	46	-	ns				
Reverse recovery time	t _{rr}	T _J = 125 °C		-	65	-					
Deels receiver a current		T _J = 25 °C	$I_{\rm F} = 30 {\rm A}$	-	21	-	А				
Peak recovery current	I _{RRM}	T _J = 125 °C	dI _F /dt = 1000 A/µs V _B = 400 V	-	36	-					
	0	T _J = 25 °C	1	-	550	-					
Reverse recovery charge	Q _{rr}	T _J = 125 °C]	-	1560	-	nC				

THERMAL - MECHANICAL SPECIFICATIONS											
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS					
Thermal resistance, junction-to-case	R _{thJC}		-	-	1.3	°C/W					
Weight			-	2.0	-	g					
Weight			-	0.07	-	oz.					
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C					
Marking device		Case style D ² PAK 2L (TO-263AB 2L)	E5TH3006SH								



VS-E5TH3006S2LHM3

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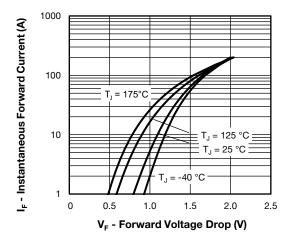


Fig. 1 - Forward Voltage Drop Characteristics, Per Leg

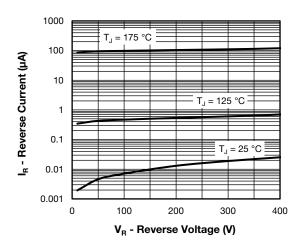
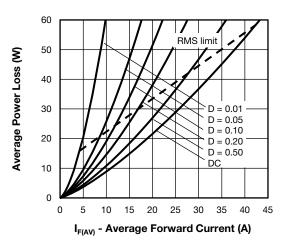
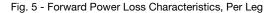


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage, Per Leg





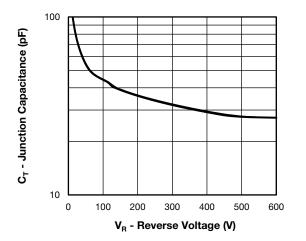
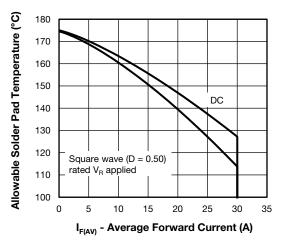
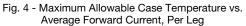


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage, Per Leg





 Revision: 12-Jun-2023
 3
 Document Number: 96837

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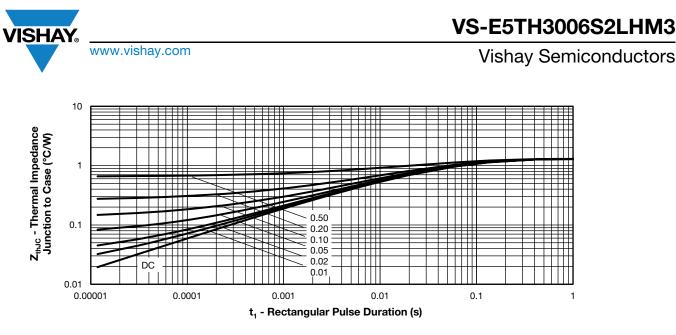


Fig. 6 - Transient Thermal Impedance, Junction to Case, Per Leg

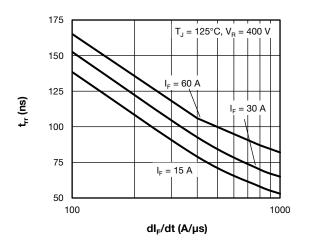


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt, Per Leg

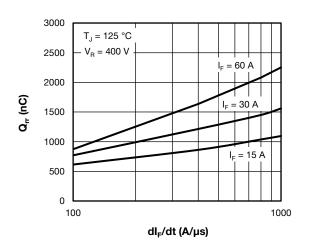


Fig. 8 - Typical Reverse Recovery Charge vs. dl_F/dt, Per Leg

45 T_J = 125 °C = 60 A 40 V_R = 400 V 35 I_F = 30 A 30 ا_ت (ک 25 20 I_{F} = 15 A 15 10 5 100 1000 dl_F/dt (A/µs)

Fig. 9 - Typical Reverse Recovery Current vs. dl_F/dt, Per Leg

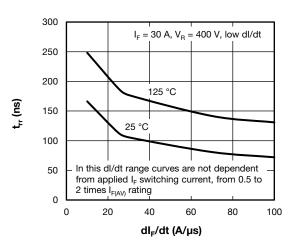


Fig. 10 - Typical Reverse Recovery Time vs. dl_F/dt, Per Leg

 Revision: 12-Jun-2023
 4
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900 In this dl/dt range curves are not dependent 800 from applied I_F switching current, from 0.5 to 2 times IF(AV) rating 700 600 Q_{rr} (nC) 500 125 °C 400 300 $I_{\rm F} = 30$ A, $V_{\rm B} = 400$ V, low dl/dt 200 100 25 °C 0 0 20 40 60 80 100 dl_F/dt (A/µs)

Fig. 11 - Typical Reverse Recovery Charge vs. dl_F/dt, Per Leg

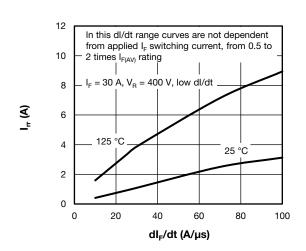


Fig. 12 - Typical Reverse Recovery Current vs. dl_F/dt, Per Leg

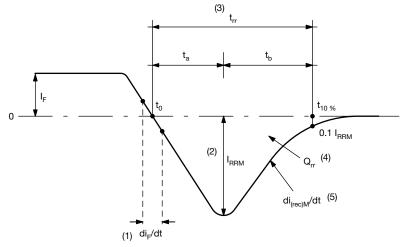


Fig. 13 - Reverse Recovery Waveform and Definitions

Notes

- $^{(1)}$ di_F/dt rate of change of current through zero crossing
- ⁽²⁾ I_{RRM} peak reverse recovery current
- $^{(3)}$ t_{rr} reverse recovery time measured from t₀, crossing point of negative going I_F, to point t_{10%}, 0.1 I_{RRM}
- $^{(4)}~Q_{rr}$ area under curve defined by t_0 and $t_{10~\%}$

$$Q_{rr} = \int_{10\%}^{t_{10\%}} I(t) dt$$

 $^{(5)}$ di_(rec)M/dt - peak rate of change of current during t_b portion of t_{rr}

VS-E5TH3006S2LHM3

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Device code	VS-	Е	5	т	н	30	06	S2	L	н	М3
		2	3	4	5	6	7	8	9	10	(11)
	 Vishay Semiconductors product E = single diode 										
	3 - 5 = FRED generation 5 4 - Package:										
	$T = D^{2}PAK (TO-262) package$ $H = hyperfast recovery$										
	 6 - Current rating (30 = 30 A) 7 - Voltage rating (06 = 600 V) 										
	 8 - S2 = true 2 pin D²PAK 9 - None = tube (50 pieces) • L = tape and real (left oriented for D²PAK package) 										
	 L = tape and reel (left oriented, for D²PAK package) If needed different orientation/packaging, please contact factory H = AEC-Q101 qualified 								,		
	11 -		vironmer = halog	•		complia	ant, and	termina	ation lea	d (Pb)-f	ree

ORDERING INFORMATION (Example)							
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION					
VS-E5TH3006S2LHM3	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?96683						
Part marking information	www.vishay.com/doc?96693						
Packaging information	www.vishay.com/doc?95032						
SPICE model	www.vishay.com/doc?96919						

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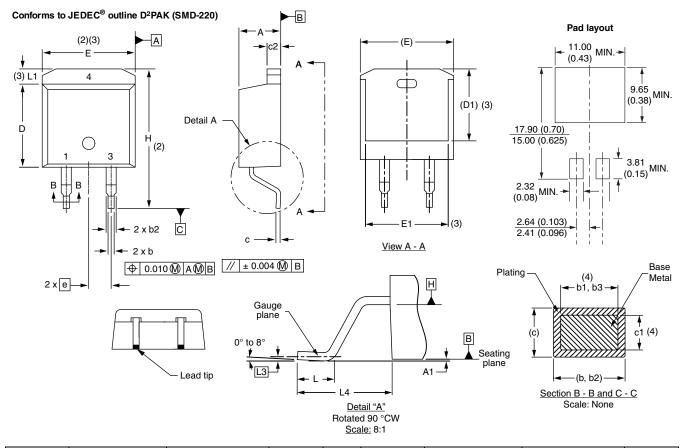


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D²PAK 2L (TO-263AB 2L)

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES	NOTES SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
с	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L3	0.25 BSC 0		0.010	BSC	
c2	1.14	1.65	0.045	0.065			L4	4.78	5.28	0.188	0.208	
D	8.51	9.65	0.335	0.380	2							

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
 (3) Thermal and contain antional within dimension E 1.1, D1 and E1.

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

(7) Outline conforms to JEDEC® outline TO-263AB

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1

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